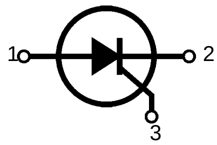
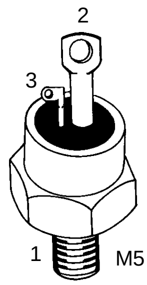
Phase Control Thyristors

V_{RRM} = 800-1200 V
$I_{T(RMS)}$ = 25 A
$I_{T(AV)M}$ = 16 A

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
900	800	CS 8-08io2
1300	1200	CS 8-12io2



TO-64



1 = Anode, 2 = Cathode, 3 = Gate

Symbol	Test Conditions		Maximum Ratings	
$I_{T(RMS)}$	T_{VJ} = T_{VJM}		25	A
$I_{T(AV)M}$	T_{case} = 85°C; 180° sine		16	A
I_{TSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	250	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	270	A
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	200	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	220	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	310	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	306	A^2s
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	200	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	200	A^2s
$(di/dt)_{cr}$	T_{VJ} = T_{VJM} f = 50 Hz, t_P =200 µs V_D = 2/3 V_{DRM}	repetitive, I_T = 48 A	150	A/µs
	I_G = 0.2 A di_G/dt = 0.2 A/µs	non repetitive, I_T = $I_{T(AV)M}$	500	A/µs
$(dv/dt)_{cr}$	T_{VJ} = T_{VJM}; R_{GK} = ∞; method 1 (linear voltage rise)	V_{DR} = 2/3 V_{DRM}	1000	V/µs
P_{GM}	T_{VJ} = T_{VJM}	t_P = 30 µs	10	W
	I_T = $I_{T(AV)M}$	t_P = 300 µs	5	W
$P_{G(AV)}$			0.5	W
V_{RGM}			10	V
T_{VJ}			-40...+125	°C
T_{VJM}			125	°C
T_{stg}			-40...+125	°C
M_d	Mounting torque		2.5	Nm
			22	lb.in.
Weight			6	g

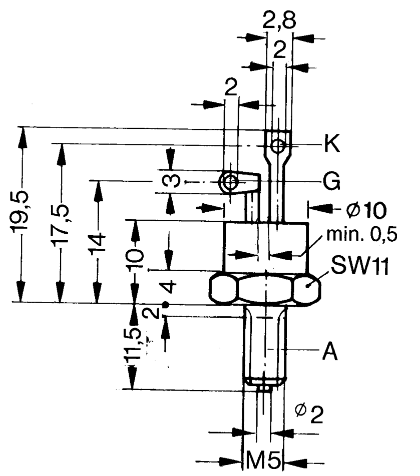
Data according to IEC 60747
IXYS reserves the right to change limits, test conditions and dimensions

Features
- Thyristor for line frequencies
- International standard package JEDEC TO-64
- Planar glassivated chip
- Long-term stability of blocking currents and voltages

Applications
- Motor control
- Power converter
- AC power controller

Advantages
- Space and weight savings
- Simple mounting
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions			Characteristic Values	
I_R, I_D	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$		≤	3	mA
V_T	I_T = 33 A; T_{VJ} = 25°C		≤	1.6	V
V_{T0} r_T	For power-loss calculations only (T_{VJ} = 125°C)			1.0 18	V mΩ
V_{GT}	V_D = 6 V;	T_{VJ} = 25°C T_{VJ} = -40°C	≤ ≤	2.5 3.5	V V
I_{GT}	V_D = 6 V;	T_{VJ} = 25°C T_{VJ} = -40°C	≤ ≤	30 50	mA mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM}$;	V_D = 2/3 V_{DRM}	≤ ≤	0.2 1	V mA
I_L	T_{VJ} = 25°C; t_P = 10 µs I_G = 0.09 A; di_G/dt = 0.09 A/µs		≤	100	mA
I_H	T_{VJ} = 25°C; V_D = 6 V; R_{GK} = ∞		≤	80	mA
t_{gd}	T_{VJ} = 25°C; V_D = 1/2 V_{DRM} I_G = 0.09 A; di_G/dt = 0.09 A/µs		≤	2	µs
t_q	$T_{VJ} = T_{VJM}$; I_T = 16 A, t_p = 300 µs; di/dt = -20 A/µs V_R = 100 V; dv/dt = 20 V/µs; V_D = 2/3 V_{DRM}		typ.	60	µs
R_{thJC} R_{thJH}	DC current DC current			1.5 2.5	K/W K/W
d_S d_A **a**	Creepage distance on surface Strike distance through air Max. acceleration, 50 Hz			1.55 1.55 50	mm mm m/s^2

Accessories:
Nut M5 DIN 439/SW8
Lock washer A5 DIN 128

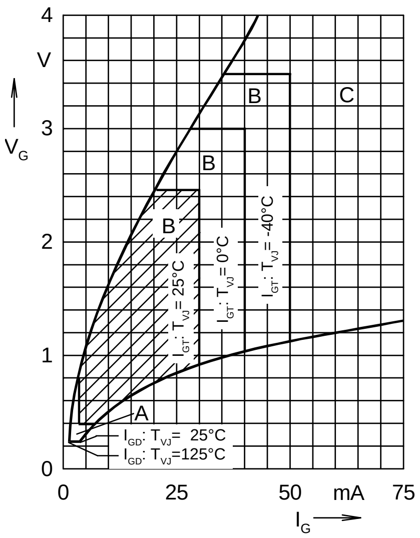


Fig. 1 Gate voltage and gate current
Triggering:
A = no; B = possible; C = safe

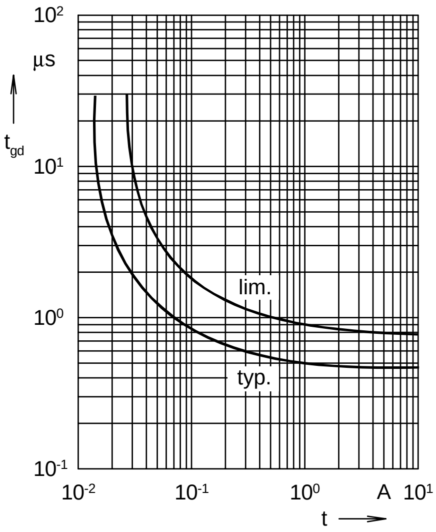


Fig. 2 Gate controlled delay time t_{gd}

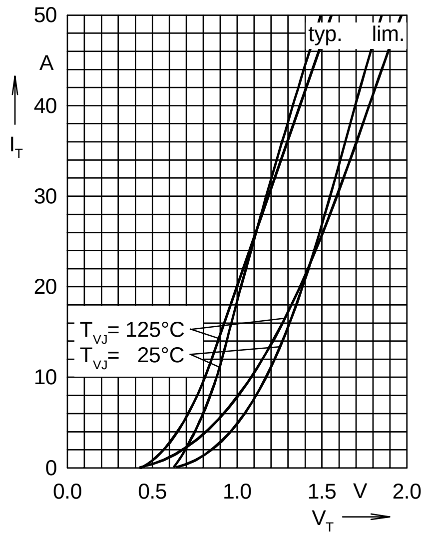


Fig. 3 On-state characteristics

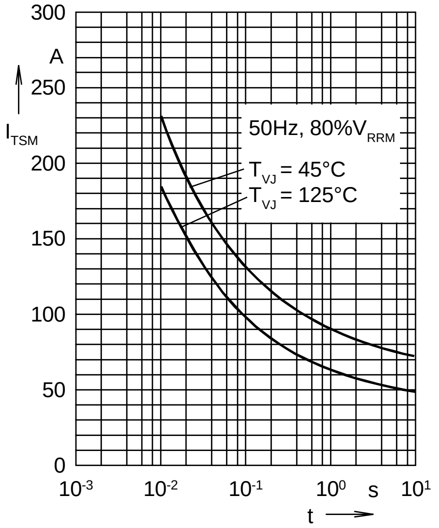


Fig. 4 Surge overload current
I_{TSM}: crest value, t: duration

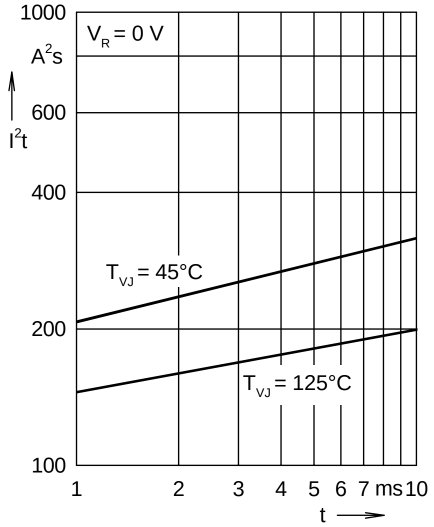


Fig. 5 I^2t versus time (1-10 ms)

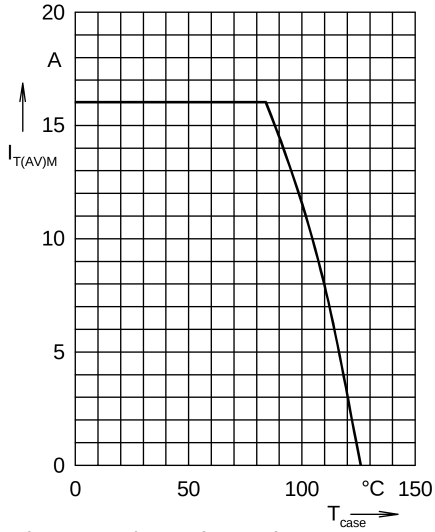


Fig. 6 Maximum forward current at case temperature 180° sine

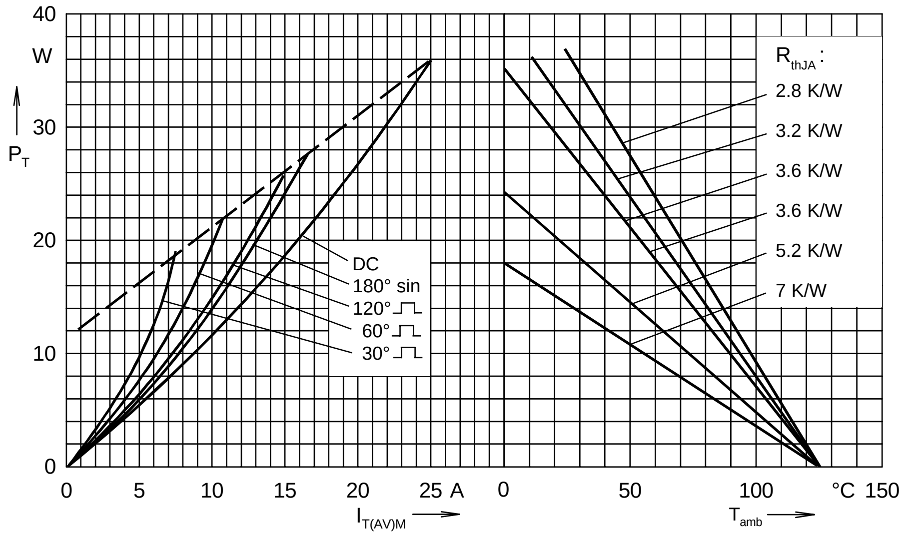


Fig. 7 Power dissipation versus on-state current and ambient temperature

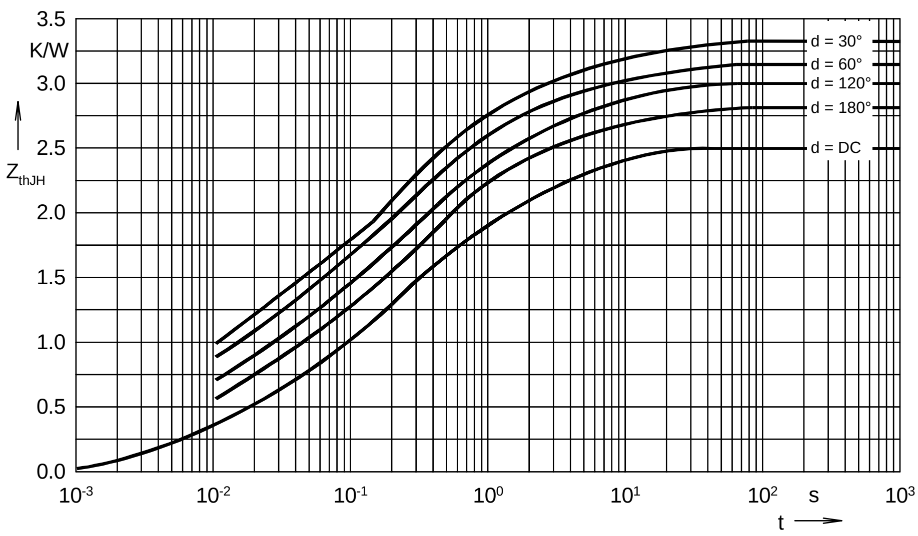


Fig. 8 Transient thermal impedance junction to heatsink

R_{thJH} for various conduction angles d:

d	R_{thJH} (K/W)
DC	2.5
180°	2.79
120°	2.95
60°	3.17
30°	3.32

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.252	0.005
2	0.333	0.0225
3	0.5	0.145
4	0.833	0.43
5	0.416	2.75
6	0.166	23